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# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

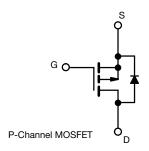


PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-40				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0034				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0048				
I <sub>D</sub> (A)	-120				
Configuration	Single				
Package	TO-263				

### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- · Package with low thermal resistance
- 100 % Rg and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \degree C$ , unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	-40	v		
Gate-source voltage		V <sub>GS</sub>	± 20	v		
Continuous drain current	$T_{C} = 25 \ ^{\circ}C \ ^{a}$	- I <sub>D</sub> -	-120			
	T <sub>C</sub> = 125 °C		-90			
Continuous source current (diode conduction	IS	-120	A			
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	-315				
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-51			
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	130	mJ		
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Po	157	W		
	T <sub>C</sub> = 125 °C		52			
Operating junction and storage temperature r	ange	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-case (drain)		R <sub>thJC</sub>	0.95	0/10		

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•		•				
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = -250 μA		-40	-	-	v	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA		-	-2.5	v	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	0 V V <sub>DS</sub> = -40 V		-	-1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-250		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 V$	-50	-	-	Α	
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -25 A	-	0.00283	0.00340		
<b>D</b> · · · · · · · ·	-	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -25 A, T <sub>J</sub> = 125 °C	-	-	0.00520	Ω	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -25 A, T <sub>J</sub> = 175 °C	-	-	0.00620		
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -20 A	-	0.00400	0.00480		
Forward transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	V <sub>DS</sub> =	-15 V, I <sub>D</sub> = -25 A	-	92	-	S	
Dynamic <sup>b</sup>	_					<u> </u>		
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -25 V, f = 1 MHz	-	17 027	23 600		
Output capacitance	Coss	$V_{GS} = 0 V$		-	1487	2100	pF	
Reverse transfer capacitance	C <sub>rss</sub>			-	1079	1500		
Total gate charge <sup>c</sup>	Qg			-	288	450	nC	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> = -20 V, I <sub>D</sub> = -60 A	-	66	-		
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	52	-		
Gate resistance	Rg		f = 1 MHz		2.65	4	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		V <sub>DD</sub> = -20 V. B <sub>l</sub> = 0.33 Ω		18	30		
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =			20	40	ns	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -60 \text{ A},  V_{\text{GEN}} = -10 \text{ V},  \text{R}_{\text{g}} = 1 \Omega$		-	155	300		
Fall time <sup>c</sup>	t <sub>f</sub>			-	135	250		
Source-Drain Diode Ratings and Charac	teristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-315	Α	
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -50 A, V <sub>GS</sub> = 0 V		-	-0.85	-1.5	V	
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = -50 A, di/dt = 100 A/μs		-	33	70	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>			-	29	60	nC	
Reverse recovery fall time	ta			-	18	-		
Reverse recovery rise time	t <sub>b</sub>			-	15	-	ns	
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>				-1.7	-	А	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

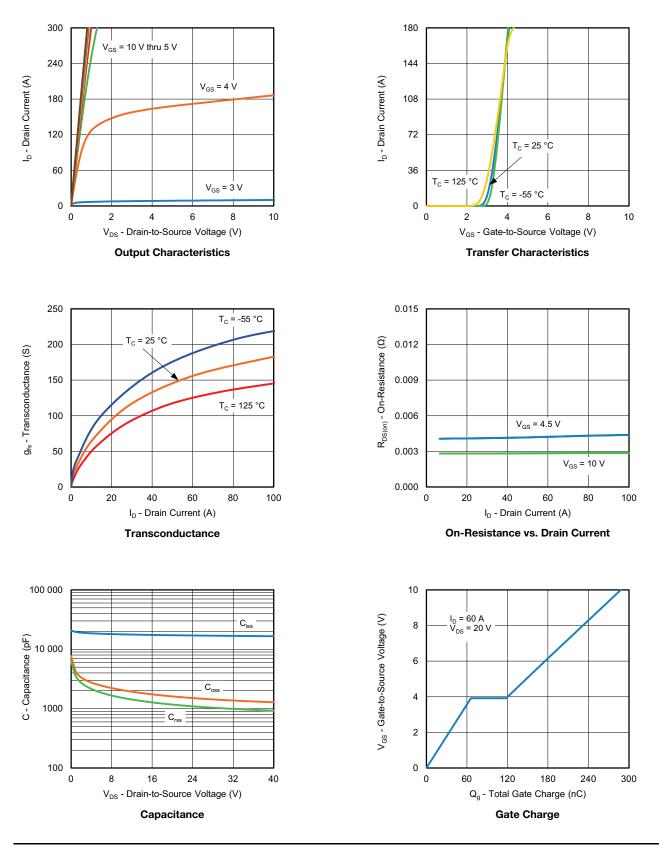
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S18-1269-Rev. A, 24-Dec-2018

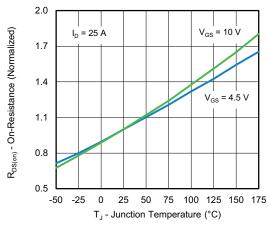
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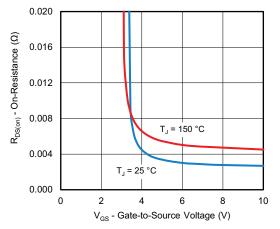


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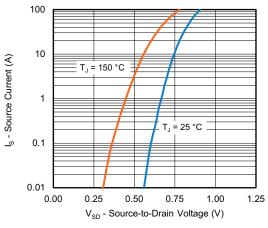
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



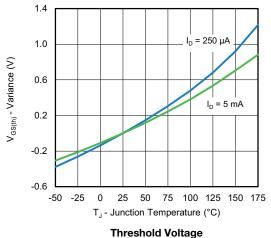
**On-Resistance vs. Junction Temperature** 



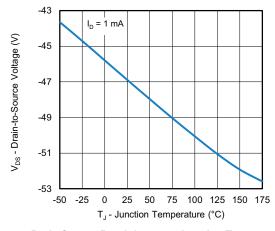
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Theorem Voltage



Drain Source Breakdown vs. Junction Temperature

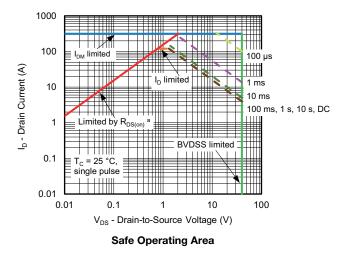
4

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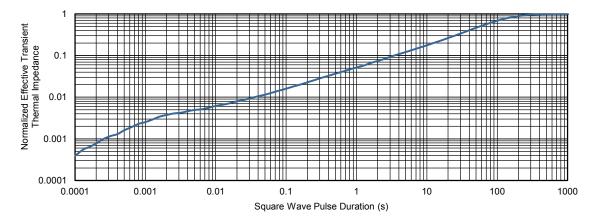
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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



#### Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(\text{on})}$  is specified



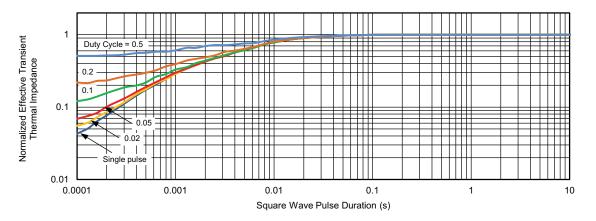
Normalized Thermal Transient Impedance, Junction-to-Ambient



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Document Number: 77450

### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

S18-1269-Rev. A, 24-Dec-2018

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
<u>1</u>	Thin lead	0.013	0.017	0.330	0.431	
c1	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	К	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

#### Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB.
  - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



## **RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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